

In the Claims:

1.-6. (Cancelled)

7. (Currently Amended) A method of tuning an active radio frequency (RF) device, the method employing tuning an impedance matching circuit coupled to the device, the matching circuit including an adjustable length transmission line, the method comprising:

providing a transmission line having an initial transmission line length of slightly more than $\frac{1}{4}$ of a wavelength of a fundamental frequency;

determining the source and load impedance of the device;

determining the characteristics of the matching circuit according to the initially determined source and load impedance;

measuring a performance characteristic of the device; and

adjusting the length of the transmission line to adjust the measured performance characteristic.

8. (Original) The method of claim 7, wherein the performance characteristic is input return loss.

9. (Original) The method of claim 7, wherein the performance characteristic is output return loss.

10. (Original) The method of claim 7, wherein the performance characteristic is gain.

11. (Original) The method of claim 7, wherein the length of the transmission line is adjusted by laser trimming the transmission line.

12. (Original) The method of claim 7, wherein the active device is a field effect transistor.

13. (Currently Amended) A method of manufacturing a power amplifier, comprising:
providing a transmission line having an initial transmission line length of slightly more than $\frac{1}{4}$ of a wavelength of a fundamental frequency;

determining the source and load impedance of the device;
determining the characteristics of the matching circuit according to the initially determined source and load impedance;
coupling an active device to a matching circuit having the previously determined characteristics, the matching circuit comprising a transmission line having an adjustable length;
measuring a performance characteristic of the device; and
adjusting the length of the transmission line to achieve a change in the measured performance characteristic.

14. (Original) The method of claim 13, wherein the device is a field effect transistor.
15. (Original) The method of claim 13, wherein the length of the transmission line is adjusted by laser trimming the transmission line.
16. (Original) The method of claim 13, wherein the performance characteristic is input return loss.
17. (Original) The method of claim 13, wherein the performance characteristic is output return loss.
18. (Original) The method of claim 13, wherein the performance characteristic is gain.